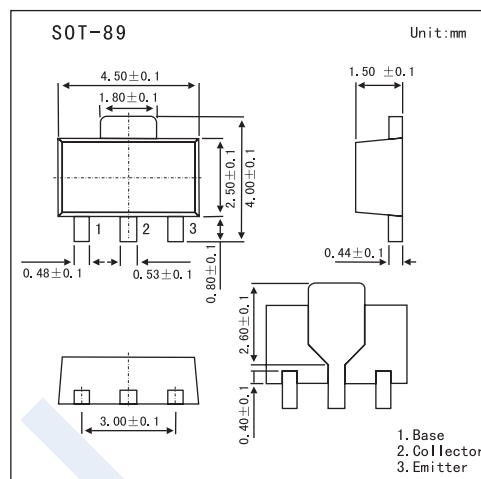


Medium Power Transistor

2SB1132

■ Features

- Low $V_{CE(sat)}$
- Compliments to 2SD1664

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-32	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current (DC) Single pulse, $P_w=100\text{ms}$	I_C	-1	A
		-2	A
Collector Power Dissipation	P_C *	0.5	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$

* mounted on a 40x40x0.7mm ceramic board.

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

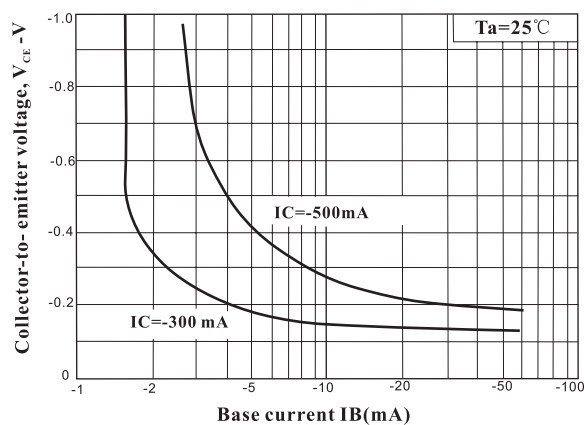
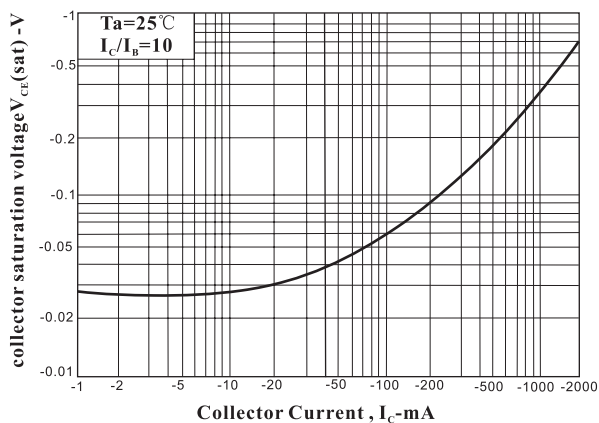
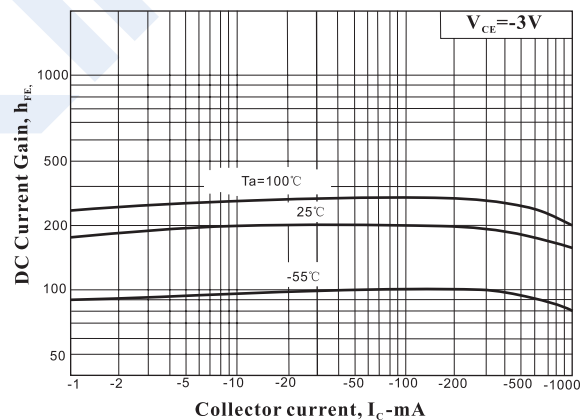
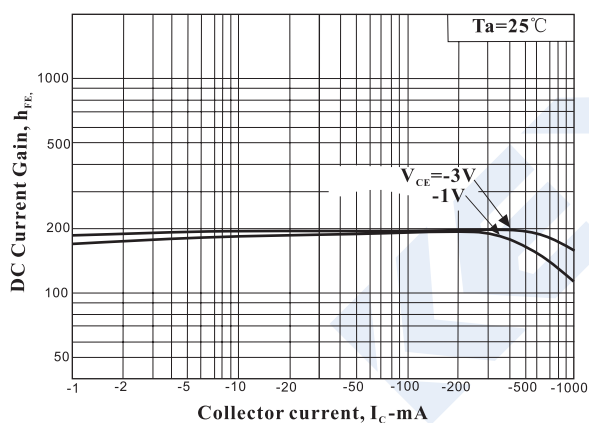
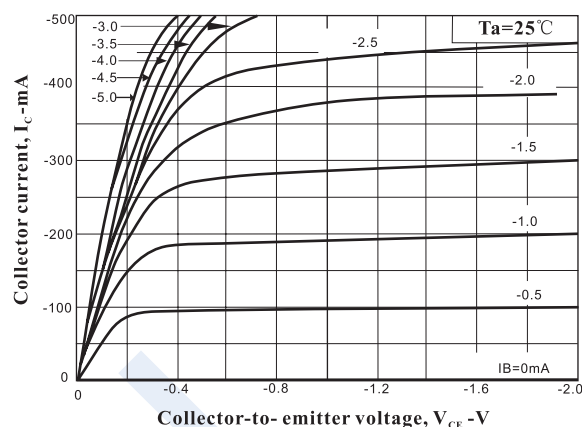
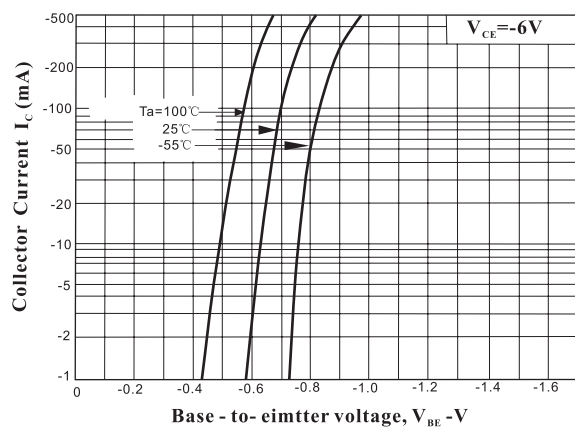
Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector Cut-off Current	I_{CBO}	$V_{CB} = -20\text{V}$, $I_E = 0$			-0.5	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -4\text{V}$, $I_C = 0$			-0.5	μA
Collector-base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -50\mu\text{A}$, $I_E = 0$	-40			V
Collector-emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}$, $I_B = 0$	-32			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -50\mu\text{A}$	-5			V
DC Current Gain	h_{FE}	$V_{CE} = -3\text{V}$, $I_C = -0.1\text{A}$	82		390	
Transition Frequency	f_T	$V_{CE} = -5\text{V}$, $I_E = 50\text{mA}$, $f = 30\text{MHz}$		150		MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$		20	30	pF

■ h_{FE} Classification

Marking	BA		
Rank	P	Q	R
h_{FE}	82 ~ 180	120 ~ 270	180 ~ 390

2SB1132

■ Electrical Characteristics Curves



2SB1132

